

P-Channel Enhancement Mode MOSFET

Feature

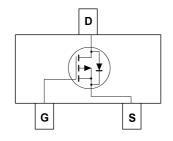
 $\bullet \quad \text{-30V/-4.2A}, \qquad \text{Rds(on)} = 55 \text{m}\Omega(\text{MAX}) \ \text{@Vgs} = \text{-10V}.$

 $RDS(ON) = 70m\Omega(MAX)$ @VGS = -4.5V.

 $RDS(ON) = 120 m\Omega(MAX) @VGS = -2.5V.$

- Super High dense cell design for extremely low RDS(ON)
- Reliable and Rugged
- SOT-23 for Surface Mount Package





Applications

• Power Management

Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings TA=25 °C Unless Otherwise noted

Parameter	Symbol	Limit	Units	
Drain-Source Voltage	$V_{ m DS}$	-30	V	
Gate-Source Voltage	V_{GS}	±12	V	
Drain Current-Continuous	I_{D}	-4.2	A	

Electrical Characteristics TA=25°C Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Тур.	Max	Units		
Off Characteristics								
Drain to Source Breakdown Voltage	BVDSS	VGS=0V, ID=-250μA	-30	-	1	V		
Zero-Gate Voltage Drain Current	IDSS	VDS=-24V, VGS=0V	-	-	-1	μΑ		
Gate Body Leakage Current, Forward	IGSSF	VGS=12V, VDS=0V	-	-	100	nA		
Gate Body Leakage Current, Reverse	IGSSR	VGS=-12V, VDS=0V	-	-	-100	nA		
On Characteristics								
Gate Threshold Voltage	VGS(th)	VGS= VDS, ID=-250 μ A	-0.7	-	-1.3	V		
Static Drain-source On-Resistance	RDS(ON)	VGS = -10V, ID = -4.2A	-	50	55	mΩ		
	1 [VGS =-4.5V, ID =-4.0A	-	60	70	mΩ		
		VGS =-2.5V, ID =-1.0A	-	80	120	mΩ		
Drain-Source Diode Characteristics and Maximum Ratings								
Drain-Source Diode Forward Voltage	VSD	VGS =0V, IS=-1.0A			-1.0	V		



Typical Characteristics

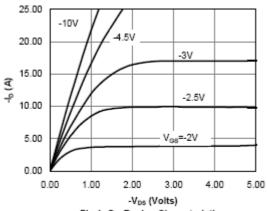


Fig 1: On-Region Characteristics

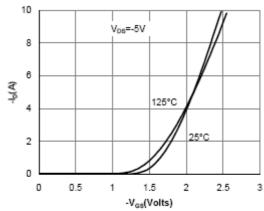


Figure 2: Transfer Characteristics

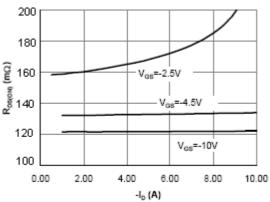
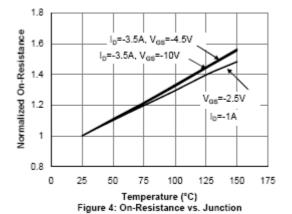


Figure 3: On-Resistance vs. Drain Current and Gate Voltage



Temperature

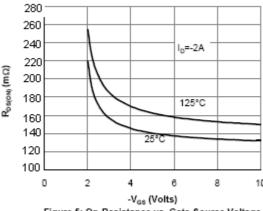


Figure 5: On-Resistance vs. Gate-Source Voltage

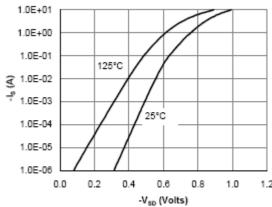
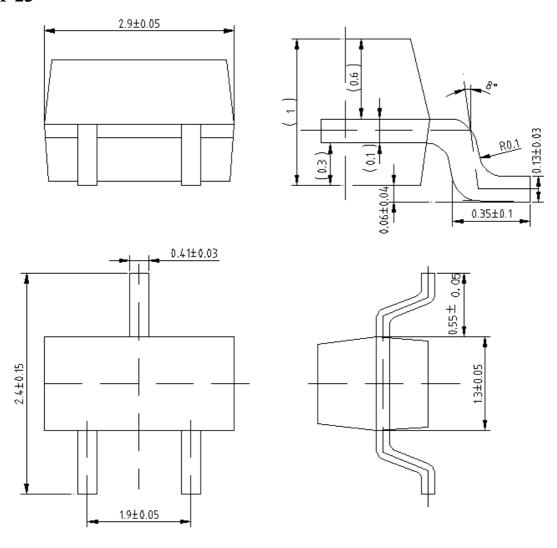


Figure 6: Body-Diode Characteristics



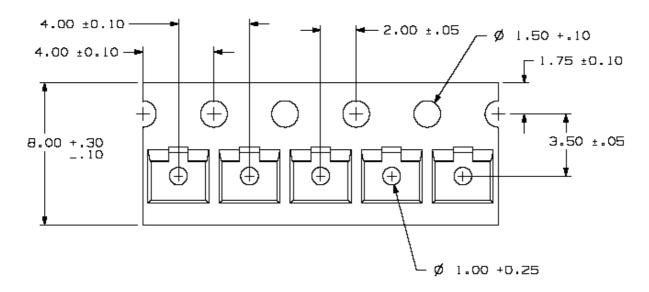
Package Outline Dimensions (UNIT: mm)

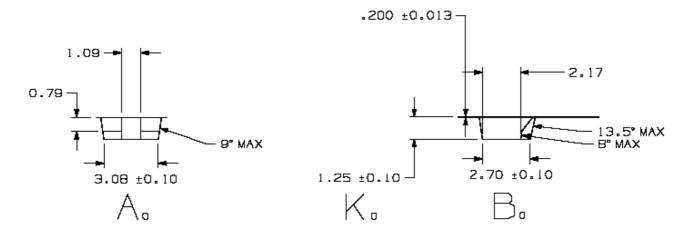
SOT-23





SOT-23 Carrier Tape







SOT-23 Carrier Reel

